

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-3. (Canceled)

1 4. (Currently Amended) An underlayer coating forming composition for forming a porous underlayer coating occupied by pores of 5 to 80% at a rate of volume for use in the manufacture of a semiconductor device, comprising a blowing agent, an organic material and a solvent, wherein a proportion of the blowing agent in solid content of the composition is 2 to 30 mass%, and wherein the blowing agent is selected from the group consisting of 4,4-oxybisbenzene sulfonyl hydrazide and azodicarbonamide.

5-6. (Canceled)

2 7. (Original) The underlayer coating forming composition according to claim 4, wherein the blowing agent is a blowing agent that is decomposed with heat to generate nitrogen, carbon dioxide or water vapor.

8. (Canceled)

3 9. (Previously Presented) The underlayer coating forming composition according to claim 4, wherein the organic material is an organic material containing at least one component selected from the group consisting of a polymer, a crosslinking compound and a light absorbing compound.

4 10. (Original) The underlayer coating forming composition according to claim 9, wherein the polymer is a polymer having at least one aromatic ring structure selected from the group consisting of a benzene ring, a naphthalene ring, an anthracene ring and a triazine ring.

5 11. (Original) The underlayer coating forming composition according to claim 9, wherein the crosslinking compound is a compound having at least two crosslink forming substituents.

6-12. (Original) The underlayer coating forming composition according to claim 9, wherein the light absorbing compound is a compound having at least one ring structure selected from the group consisting of a benzene ring, a naphthalene ring, an anthracene ring and a triazine trione ring.

2-13. (Previously Presented) A method for forming a photoresist pattern for use in the manufacture of a semiconductor device, comprising:

forming a porous underlayer coating occupied by pores of 5 to 80% at a rate of volume by applying the underlayer coating forming composition according to claim 4 on a semiconductor substrate and heating it;

forming a photoresist layer on the porous underlayer coating;

exposing the semiconductor substrate covered with the porous underlayer coating and the photoresist to light;

developing the photoresist after the exposure to light; and

removing the porous underlayer coating corresponding to a part of developed and removed photoresist by etching.